

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-5. (Canceled)

6. (Original) A capacitor assembly comprising

a storage node extending within an insulative layer, wherein the storage node is next to a layer comprising silicon, about 2% to about 20% by weight carbon and about 5% to about 75% by weight oxygen;

a second electrode proximate the storage node; and

a dielectric layer between the storage node and the second electrode.

7. (Original) The capacitor assembly of claim 6, wherein the storage node is next to a layer comprising about 20% to about 65% by weight silicon, about 0% to about 30% by weight nitrogen, about 10% to about 20% by weight carbon, and about 5% to about 25% by weight oxygen.

8. (Original) The capacitor assembly of claim 6, wherein the storage node is next to a layer comprising about 20% to about 65% by weight silicon, about 0% to about 15% by weight nitrogen, about 2% to about 10% by weight carbon, and about 40% to about 75% by weight oxygen.

9-14. (Canceled)

15. (Original) An assembly comprising

a substrate;

a layer comprising silicon, about 2% to about 20% by weight carbon and about 5% to about 75% by weight oxygen; and

a photoresist masking layer.

16. (Original) The assembly of claim 15, wherein the layer comprises about 20% to about 65% by weight silicon, about 10% to about 20% by weight carbon, about 5% to about 25% by weight oxygen and about 0% to about 30% by weight nitrogen.

17. (Original) The assembly of claim 15, wherein the layer comprises about 20% to about 65% by weight silicon, about 2% to about 10% by weight carbon, about 40% to about 75% by weight oxygen and about 0% to about 15% by weight nitrogen.

18. (New) The assembly of claim 15, wherein the photoresist masking layer is a patterned photoresist masking layer

19. (New) The assembly of claim 15, wherein the substrate is a monocrystalline wafer.

20. (New) The capacitor of claim 6, wherein the storage node comprises conductively doped silicon.

21. (New) The capacitor of claim 6, wherein the insulative layer comprises silicon oxide or silicon nitride.

22. (New) The capacitor of claim 6, wherein the dielectric layer comprises silicon dioxide or silicon nitride.